

## *Supporting Information*

### **Hydrogen-bonded CdSe/PDI with double electric field synergism for enhanced overall water splitting performance**

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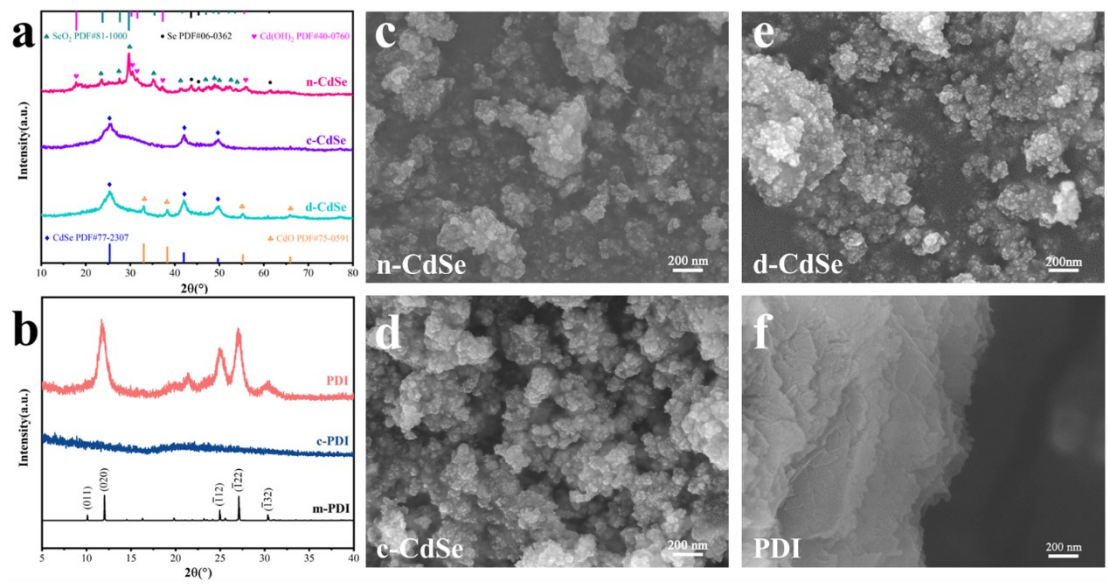


Fig. S1 XRD patterns of various CdSe (a) and PDI (b), SEM images of various CdSe (c–e) and PDI

(f)

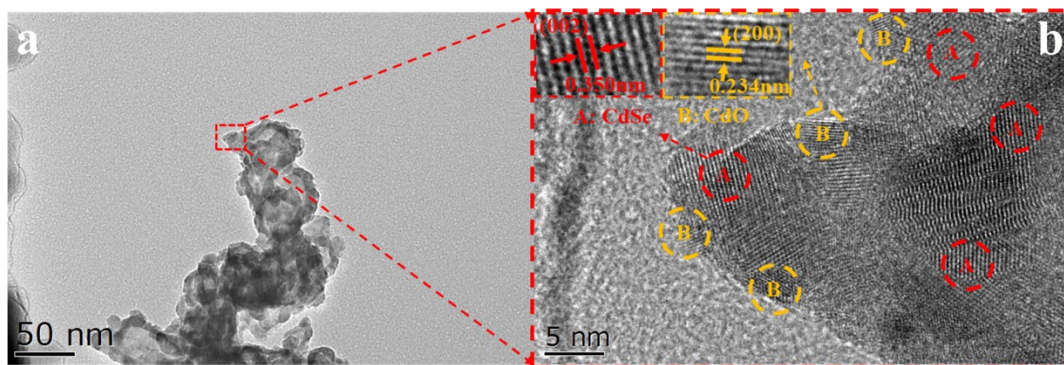


Fig. S2 TEM images (a) of d-CdSe and lattice fringes of d-CdSe (b)

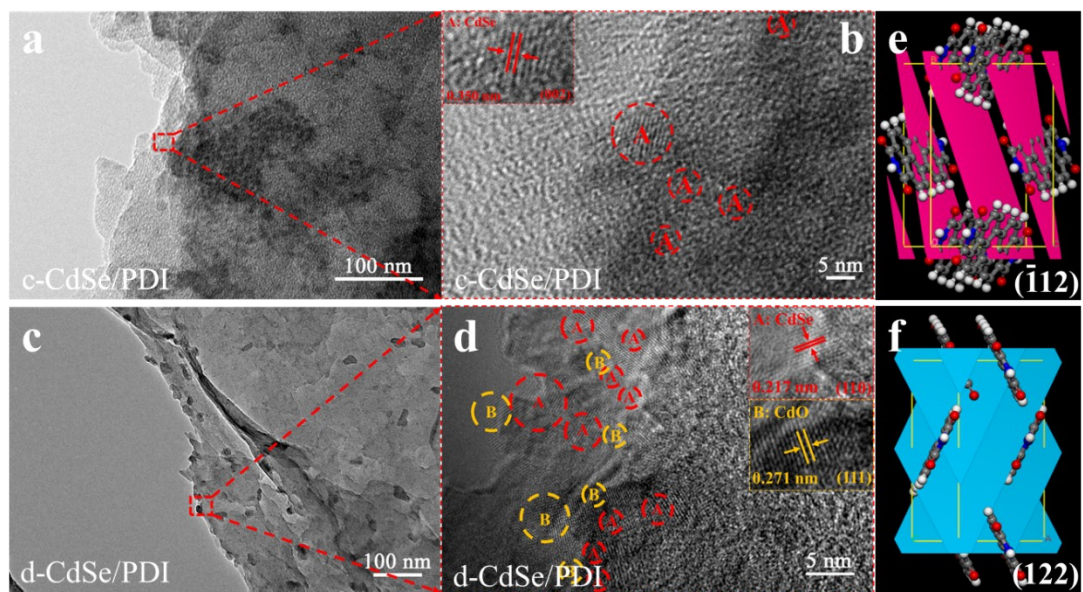


Fig. S3 TEM images of c-CdSe/PDI (a) and (b); TEM images of d-CdSe/PDI (c) and (d); and  $(\bar{1}12)$  (e) and  $(122)$  (f) crystal faces of PDI

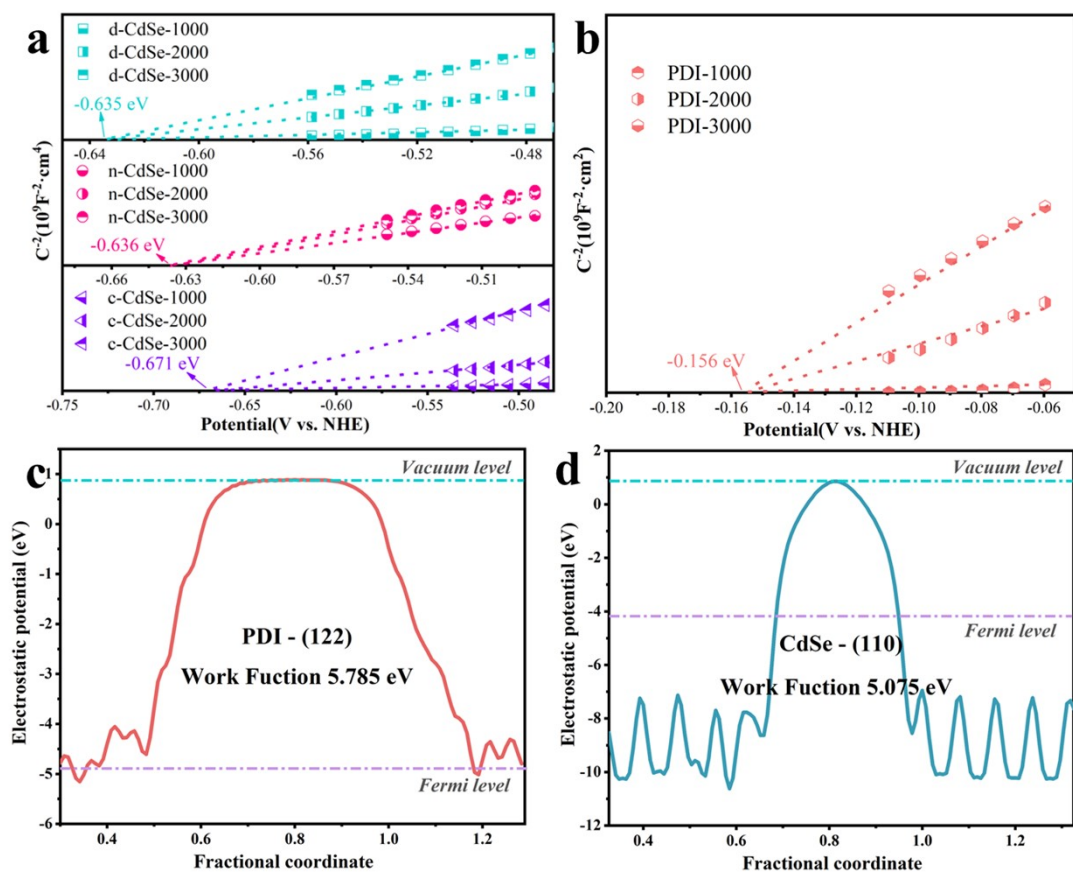


Fig. S4 Mott-Schottky curves of various CdSe (a) and PDI (b); DFT-calculated work function of PDI (112) (c) and CdSe (110) (d)

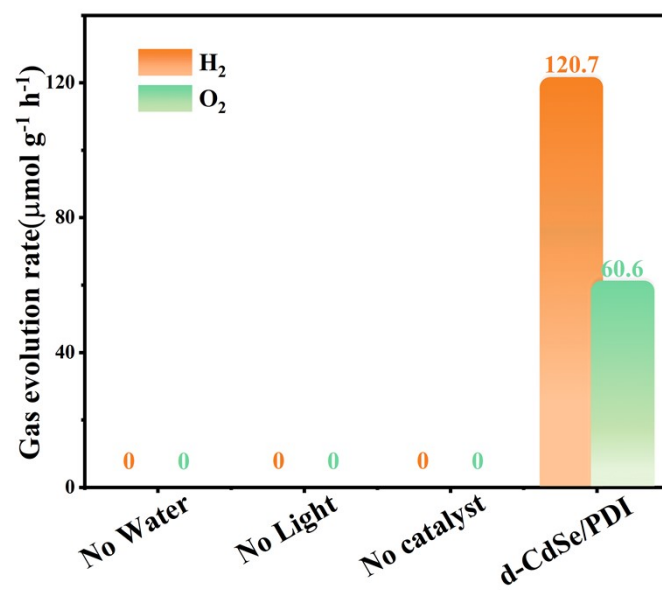


Fig. S5 Gas yield of control experiment

Table S1. Comparison of the photocatalytic water splitting activity for some representative photocatalysts

material	band gap	co-catalyst	light source	solution	gas generation rate( $\mu\text{mol g}^{-1} \text{h}^{-1}$ )	ref.
d-CdSe/PDI	1.6/2.8	--	300 W-Xe (> 380 nm)	10 mL H <sub>2</sub> O	H <sub>2</sub> :120.7 O <sub>2</sub> :60.6	This work
Cu <sub>7</sub> S <sub>4</sub> /r-MnS	0.77/2.12	MnO <sub>x</sub>	300 W-Xe (>420 nm)	6 mL H <sub>2</sub> O	H <sub>2</sub> :309 O <sub>2</sub> :36	[S1]
Cu <sub>2</sub> P/Bi <sub>2</sub> WO <sub>3</sub>	1.6/2.8	--	150 W-Xe	Na <sub>2</sub> HPO <sub>4</sub> / NaH <sub>2</sub> PO <sub>4</sub> , 80 mL	H <sub>2</sub> :4.7 O <sub>2</sub> :2.3	[S2]
P/Bi <sub>2</sub> VO <sub>3</sub>	0.7/2.39	--	320 W-Xe (> 420 nm)	8 mL H <sub>2</sub> O	H <sub>2</sub> :16 O <sub>2</sub> :102	[S3]
BP/RP	1.27/1.96	Co,Fe, Ni,Cu	200 W-LED (> 420 nm)	6 mL H <sub>2</sub> O	H <sub>2</sub> :300	[S4]
ZnTe/TiO <sub>2</sub>	2.14/3.05	Au	320 W-Xe (> 350 nm)	50 mL H <sub>2</sub> O	H <sub>2</sub> :3340 O <sub>2</sub> :1670	[S5]
C <sub>ring</sub> /C <sub>3</sub> N <sub>4</sub>	0/2.74	3 wt%Pt	300 W-Xe (>420 nm)	Pure H <sub>2</sub> O	H <sub>2</sub> :150 O <sub>2</sub> :75	[S6]
g-C <sub>3</sub> N <sub>4</sub> /TiO <sub>2</sub>	2.7/3.2	--	300 W-Xe (> 400 nm)	100 mL H <sub>2</sub> O	H <sub>2</sub> :65	[S7]

The red part is this work, the blue part is the heterojunction composed of inorganic and inorganic materials, and the yellow part is the heterojunction formed by hybridization of organic and inorganic materials.



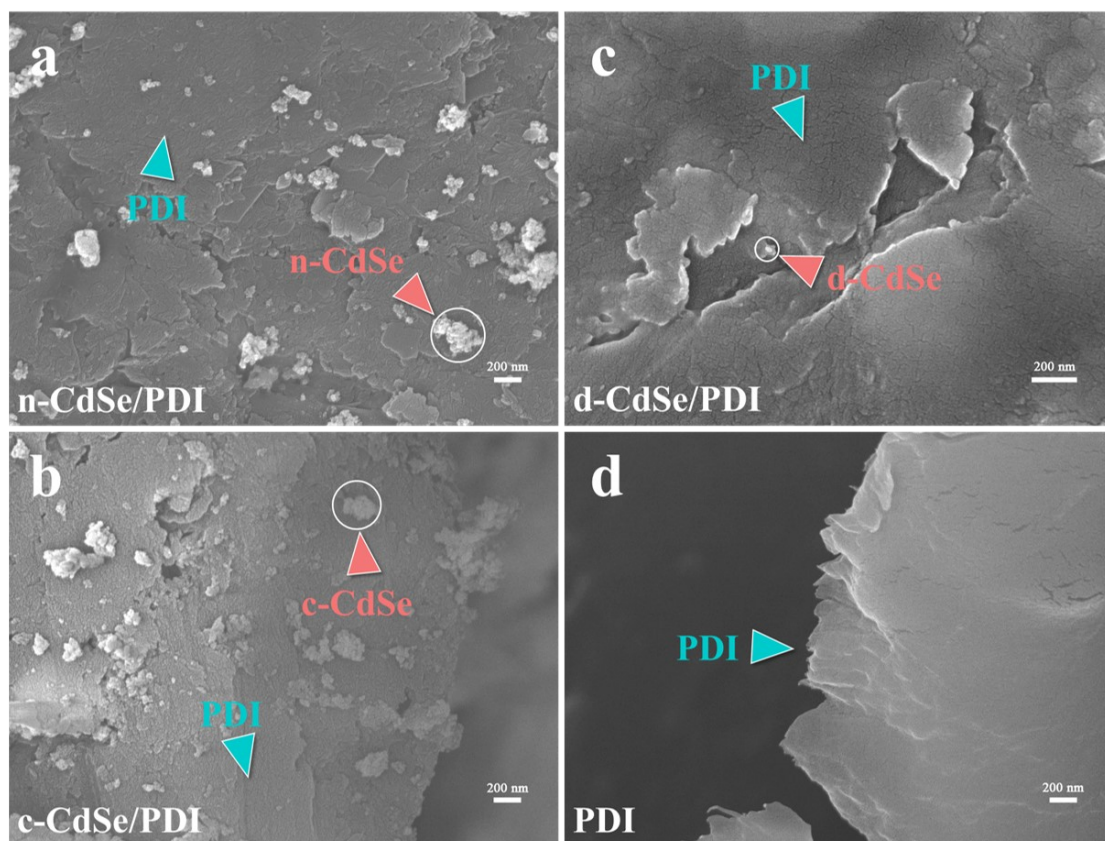


Fig. S6 SEM images of samples after reaction



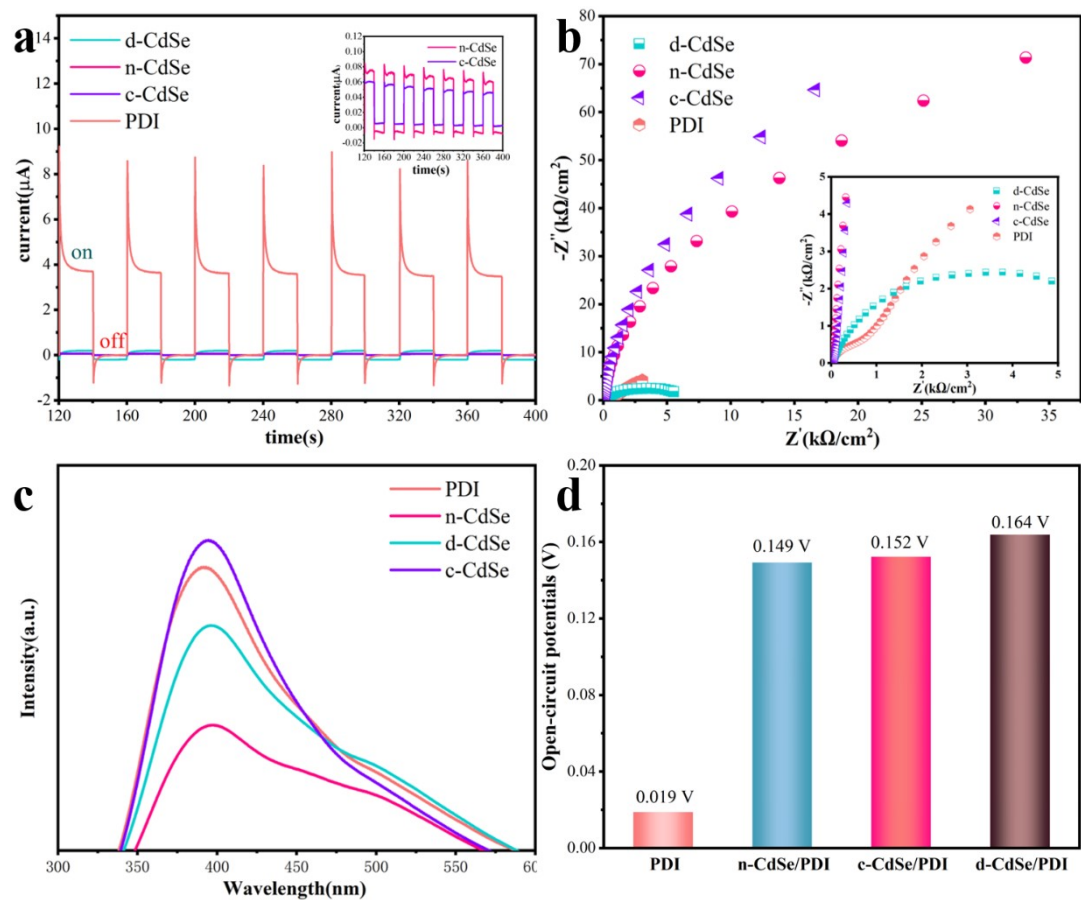


Fig. S7 *I-t* curves (a), EIS (b), and PL of single-component samples (c); open-circuit potential of PDI and composite samples (d)

The built-in electric field strength of the overall catalyst can be obtained from Eq. S1:<sup>S8</sup>

$$E = \left( \frac{-2V_s \rho}{\epsilon \epsilon_0} \right)^{1/2} \dots\dots\dots \text{Eq. S1}$$

where  $E$  is the internal electric field magnitude,  $V_s$  the surface voltage,  $\rho$  the surface charge density,  $\epsilon$  the low-frequency dielectric constant, and  $\epsilon_0$  the permittivity of free space. The above equation reveals that the internal electric field magnitude is mainly determined by the surface voltage and charge density because  $\epsilon$  and  $\epsilon_0$  are two constants.

The carrier lifetime in the TRPL can be calculated from Eq. S2:

$$\tau_{ave} = \frac{A_1 \tau_1^2 + A_2 \tau_2^2}{A_1 \tau_1 + A_2 \tau_2} \dots\dots\dots \text{Eq. S2}$$

where  $A_1$  and  $A_2$  represent the amplitudes of the fast and slow components,  $\tau_1$  and  $\tau_2$  the time constants. The fitting parameters used for our curves are listed in Table S2.

<b>Sample</b>	<b><math>\tau_1/\text{ns}</math></b>	<b><math>\tau_2/\text{ns}</math></b>	<b><math>A_1/\%</math></b>	<b><math>A_2/\%</math></b>	<b><math>\tau_{\text{ave}}/\text{ns}</math></b>
<b>d-CdSe</b>	0.29	4.32	88.85	11.15	2.92
<b>PDI</b>	0.28	3.21	90.93	9.07	1.84
<b>d-CdSe/PDI</b>	0.29	4.72	87.74	12.26	3.37

Table S2. Fitting parameters for transient PL spectra

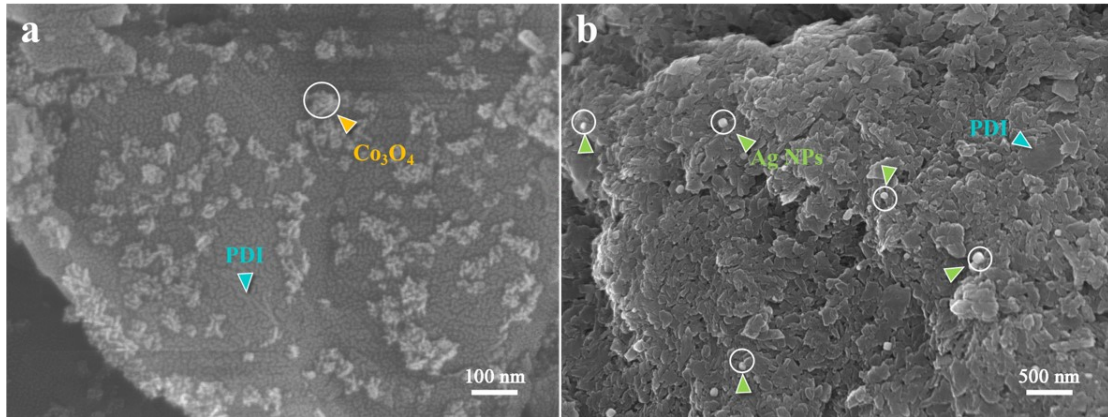


Fig. S8 Morphology of Co<sub>3</sub>O<sub>4</sub> and Ag nanoparticles loaded on PDI, respectively

We determined the hole accumulation and electron accumulation surfaces of PDI by the position of photodeposited Co<sub>3</sub>O<sub>4</sub> and Ag nanoparticles loaded on PDI nanosheets. The surface where Co<sub>3</sub>O<sub>4</sub> is located is the hole accumulation surface, and the surface where Ag nanoparticles are located is the electron accumulation surface. It can be observed from Fig. S8 that Co<sub>3</sub>O<sub>4</sub> is loaded on the front side of PDI nanosheets and Ag nanoparticles are loaded on the side of PDI nanosheets. Therefore, the side of PDI nanosheet (122) is the electron accumulation surface and the front side (-112) is the hole accumulation surface.

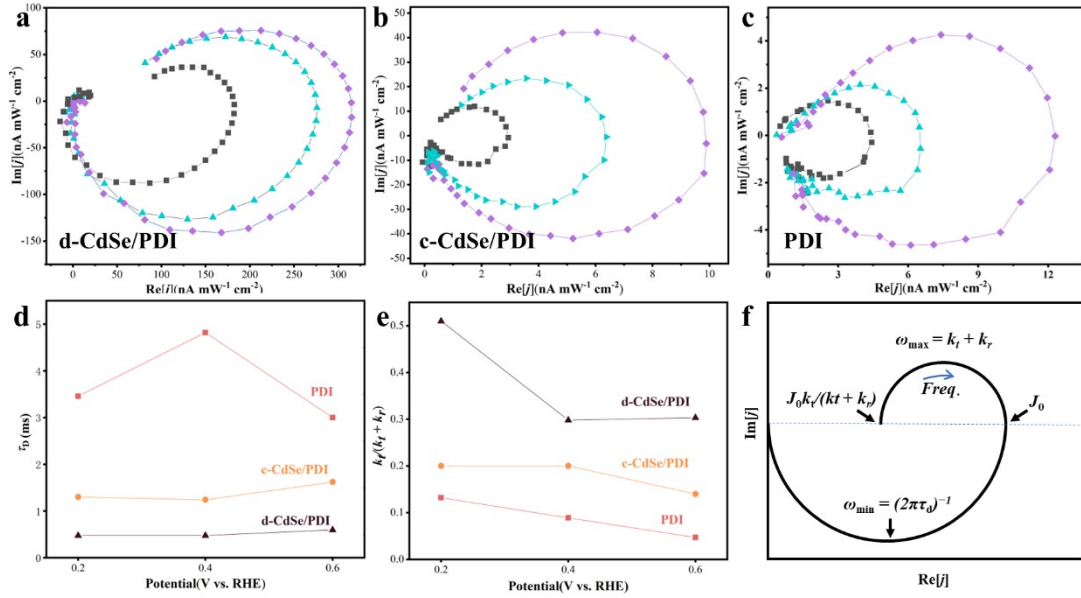


Fig. S9 IMPS of d-CdSe/PDI (a), c-CdSe/PDI (b), and PDI (c) measured at 0.2, 0.4 and 0.6 V vs. NHE;  $\tau_D$  (d) and  $k_f/(k_t + k_r)$  (e) values extracted from the IMPS fitting data at different potentials; and schematic diagram of the IMPS mathematical model (f)

Intensity-modulated photocurrent spectra (IMPS) allows further quantitative analysis of the carrier dynamics in the sample. The intensity-modulated photocurrent response  $j(\omega)$  is shown in Eq. S3:<sup>S9</sup>

$$j(\omega) = j_0 \times \frac{k_t + i\omega \left( \frac{C_H}{1 + C_H/C_{SC}} \right)}{k_t + k_r + i\omega} \times \frac{1}{1 + i\omega\tau_D} \dots\dots\dots \text{Eq. S3}$$

Where  $j_0$  is the hole amplitude of the hole flow to the surface,  $C_{SC}$  and  $C_H$  are the point capacitances of the space charge layer and the Helmholtz layer,  $k_t$  and  $k_r$  are the pseudo-first-order rate constants for charge transfer and complexation,  $\tau_D$  is the average transport time of the photogenerated electrons,  $\omega$  is the frequency of the modulated light and  $i$  is the current. It can be seen from Fig. S9f that in the low-frequency semicircle, the real part at  $\omega = 0$  is close to  $j_0 k_t / (k_t + k_r)$ , and  $\omega_{\max} = k_t + k_r$  can satisfy its maximum value. The high-frequency intercept of the composite semicircle corresponds to the instantaneous photocurrent, and the value of the real part tends to  $j_0$ . The value of  $\tau_D$  is related to the frequency of the lowest point of the imaginary part. Therefore, the values of  $j_0$ ,  $\tau_D$ ,  $k_t$  and  $k_r$  can be calculated from the high frequency intercept, the low frequency intercept,  $\omega_{\max}$  and  $\omega_{\min}$ . Typically,  $\tau_D$  is considered to be a metric of charge bulk phase transport, and the larger its value, the higher the bulk phase complex.<sup>S10</sup> The degree of bulk-phase complexation can be derived from Fig. S9d: d-CdSe/PDI < c-CdSe/PDI < PDI. d-CdeSe/PDI has the strongest charge-transfer capability, as can be seen from the relative magnitude of the electron-transfer efficiency,  $k_t / (k_t + k_r)$ , in Fig. S9e. It further indicates that an isotropic double electric field can synergistically promote charge transfer and transport.

## Reference

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